

SANYO

No.3484

2SC4705

NPN Epitaxial Planar Silicon Transistor

Low-Frequency General-Purpose Amp
Applications (High h_{FE})

Applications

- Low-frequency general-purpose amp, drivers, muting circuits

Features

- High DC current gain ($h_{FE} = 800$ to 3200)
- Low collector-to-emitter saturation voltage : $V_{CE(sat)} \leq 0.5V$ max
- High V_{EBO} : $V_{EBO} \geq 15V$
- Small size making it easy to provide high-density, hybrid ICs.

Absolute Maximum Ratings at $T_a = 25^\circ C$

			unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	15	V
Collector Current	I_C	200	mA
Collector Current(Pulse)	I_{CP}	300	mA
Base Current	I_B	40	mA
Collector Dissipation	P_C	Mounted on ceramic board ($250mm^2 \times 0.8mm$)	1.3 W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	- 55 to + 150	$^\circ C$

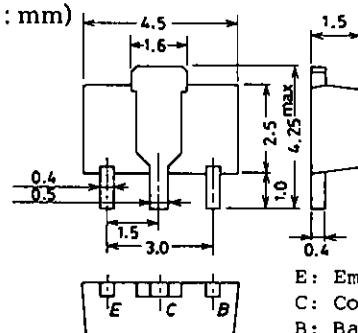
Electrical Characteristics at $T_a = 25^\circ C$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 40V, I_E = 0$			0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 10V, I_C = 0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = 5V, I_C = 100mA$	800	1500	3200	
Gain-Bandwidth Product	f_T	$V_{CE} = 10V, I_C = 10mA$		250		MHz
Output Capacitance	c_{ob}	$V_{CB} = 10V, f = 1MHz$		4.0		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 100mA, I_B = 2mA$		0.12	0.5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 100mA, I_B = 2mA$		0.85	1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	60			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA, R_{BE} = \infty$	50			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	15			V

Marking : CP

Package Dimensions 2038

(unit : mm)

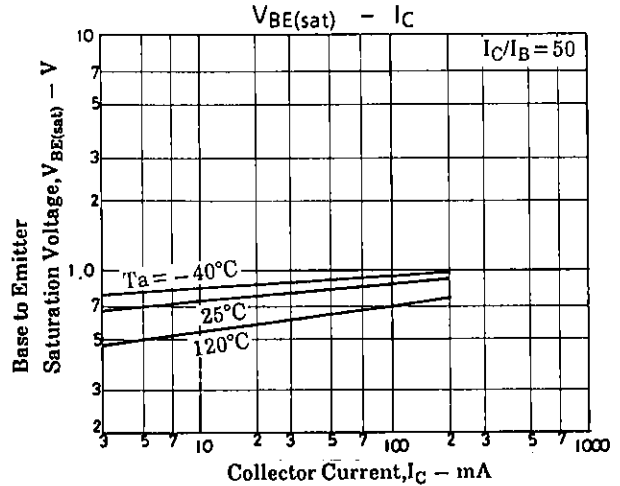
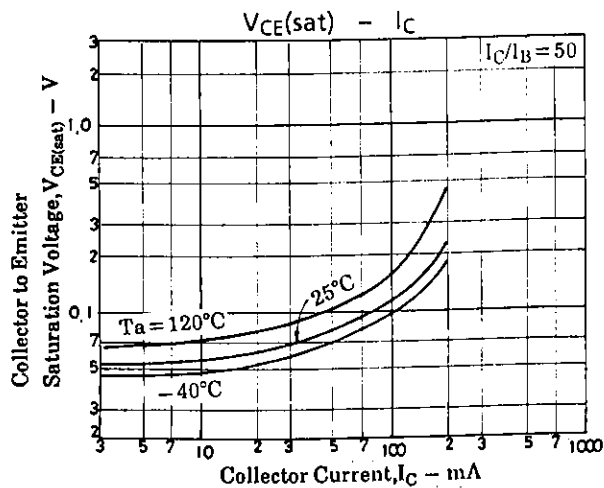
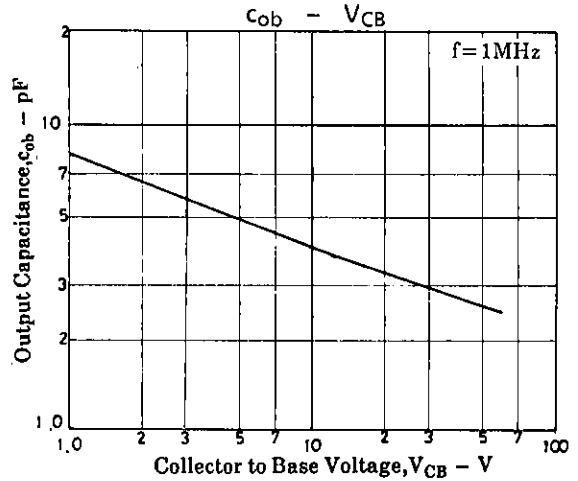
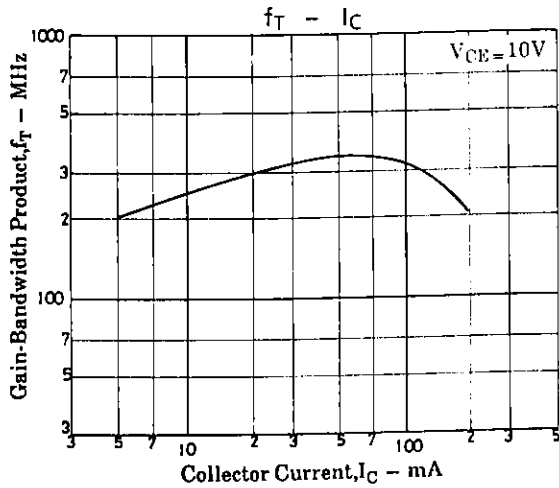
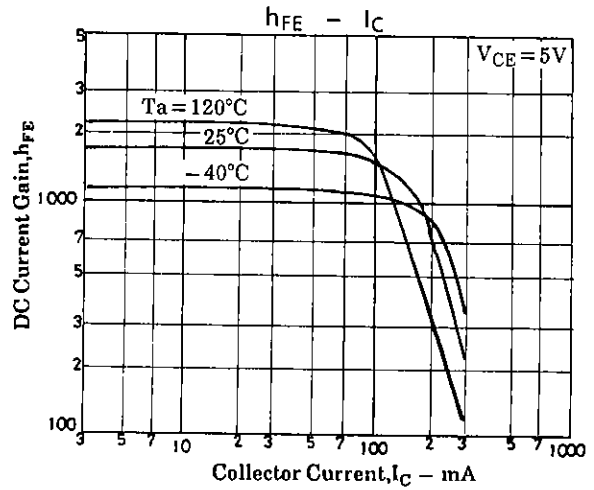
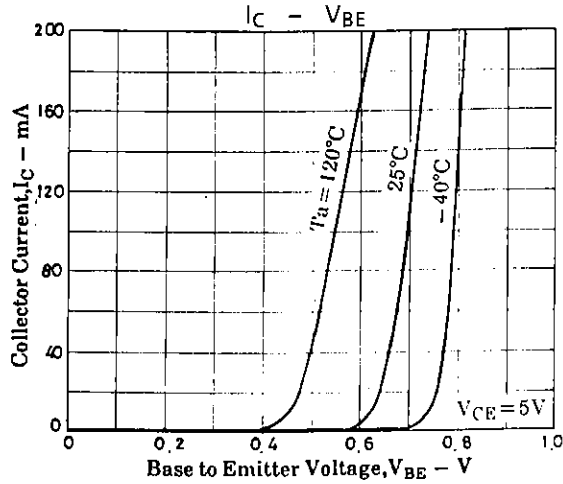
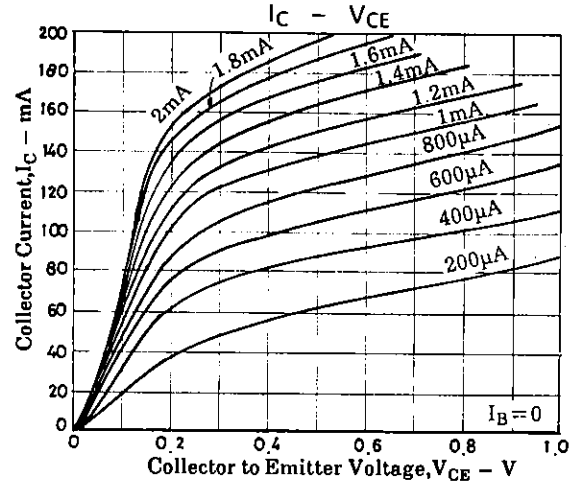
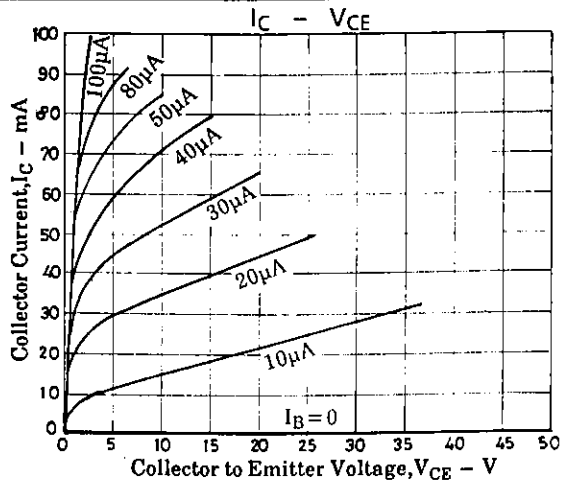


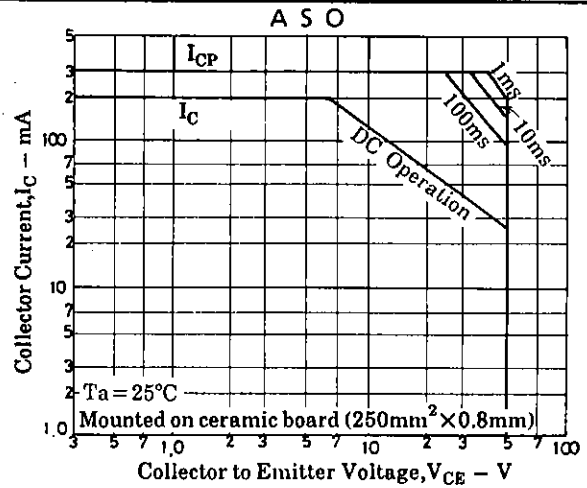
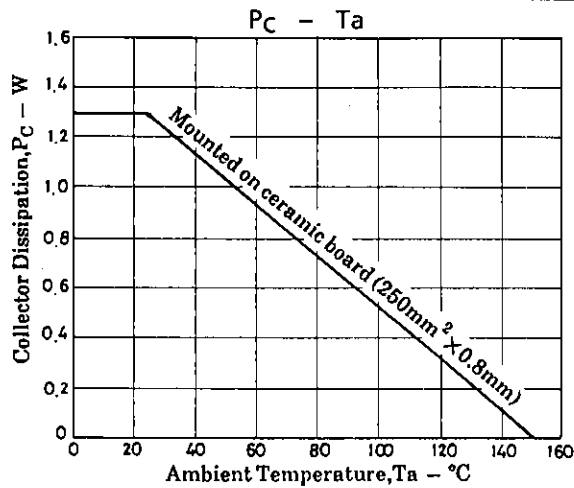
E: Emitter
C: Collector
B: Base

SANYO: PCP
(Bottom View)

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